

Michael Yakimov

List of Publications by Year in descending order

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papers

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docs citations

23
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citing authors

#	ARTICLE	IF	CITATIONS
1	Exciton-lattice polaritons in multiple-quantum-well-based photonic crystals. <i>Nature Photonics</i> , 2009, 3, 662-666.	31.4	64
2	Improvement of the GaSb/Al ₂ O ₃ interface using a thin InAs surface layer. <i>Solid-State Electronics</i> , 2012, 78, 56-61.	1.4	30
3	Dynamic Control of AlGaN/GaN HEMT Characteristics by Implementation of a p-GaN Body-Diode-Based Back-Gate. <i>IEEE Journal of the Electron Devices Society</i> , 2019, 7, 581-588.	2.1	16
4	In situ monitoring of formation of InAs quantum dots and overgrowth by GaAs or AlAs. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005, 23, 1221.	1.6	12
5	In Situ Deposited HfO ₂ with Amorphous-Si Passivation as a Potential Gate Stack for High Mobility (In)GaSb- Based P-MOSFETs. <i>ECS Transactions</i> , 2011, 41, 223-230.	0.5	11
6	Electron Scattering in Buried InGaAs/High-k MOS Channels. <i>ECS Transactions</i> , 2011, 35, 385-395.	0.5	10
7	Investigation of arsenic and antimony capping layers, and half cycle reactions during atomic layer deposition of Al ₂ O ₃ on GaSb(100). <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2013, 31, .	2.1	10
8	CHALLENGES AND PROGRESS IN III-V MOSFETs FOR CMOS CIRCUITS. <i>International Journal of High Speed Electronics and Systems</i> , 2008, 18, 761-772.	0.7	7
9	Integrated Semiconductor Quantum Dot Scintillation Detector: Ultimate Limit for Speed and Light Yield. <i>IEEE Transactions on Nuclear Science</i> , 2016, 63, 656-663.	2.0	7
10	Drain-Voltage-Induced Secondary Effects in AlGaIn/GaN HEMTs With Integrated Body-Diode. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 3983-3987.	3.0	6
11	Structural and Optical Effects of Capping Layer Material and Growth Rate on the Properties of Self-Assembled InAs Quantum Dot Structures. <i>Materials Research Society Symposia Proceedings</i> , 2004, 829, 142.	0.1	5
12	Hole mobility and remote scattering in strained InGaSb quantum well MOSFET channels with Al ₂ O ₃ oxide. <i>Physica Status Solidi - Rapid Research Letters</i> , 2013, 7, 550-553.	2.4	5
13	Interface trap density and mobility extraction in InGaAs buried quantum well metal-oxide-semiconductor field-effect-transistors by gated Hall method. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	5
14	GaSb on Si: Structural Defects and Their Effect on Surface Morphology and Electrical Properties. <i>Materials Research Society Symposia Proceedings</i> , 2014, 1635, 115-120.	0.1	5
15	Development of III-Sb Technology for p-Channel MOSFETs. <i>International Journal of High Speed Electronics and Systems</i> , 2014, 23, 1450015.	0.7	4
16	Strained Quantum Wells for P-channel InGaAs CMOS. <i>Materials Research Society Symposia Proceedings</i> , 2008, 1108, 1.	0.1	2
17	InGaAs and GaAs/InGaAs Channel Enhancement Mode n-MOSFETs With HfO ₂ Gate Oxide and a-Si Interface Passivation Layer. <i>Device Research Conference, IEEE Annual</i> , 2007, , .	0.0	1
18	CHALLENGES AND PROGRESS IN III-V MOSFETs FOR CMOS CIRCUITS. <i>Selected Topics in Electornics and Systems</i> , 2009, , 3-14.	0.2	1

#	ARTICLE	IF	CITATIONS
19	Development of III-Sb Technology for p-Channel MOSFETs. , 2015, , .		1
20	Tunnel QW-QDs InGaAs-InAs High Gain Medium for All-Epitaxial VCSELs. Materials Research Society Symposia Proceedings, 2006, 959, 1.	0.1	0
21	Optical properties of InAs quantum dot structures transferred to Si with oxidation lift-off technology. , 2006, , .		0
22	Group III-Sb Metamorphic Buffer on Si for p-Channel all-III-V CMOS: Electrical Properties, Growth and Surface Defects. Materials Research Society Symposia Proceedings, 2015, 1790, 13-18.	0.1	0
23	Anomalous minority carrier behavior induced by chemical surface passivation solution in p-type GaSb metal-oxide-semiconductor capacitors on Si substrates. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2020, 38, 052204.	1.2	0